查询IDT54FCT521ADB供应商

Integrated Device Technology, Inc.

FAST CMOS 8-BIT IDENTITY COMPARATOR

IDT54/74FCT521
IDT54/74FCT521A
IDT54/74FCT521B
IDT54/74FCT521C

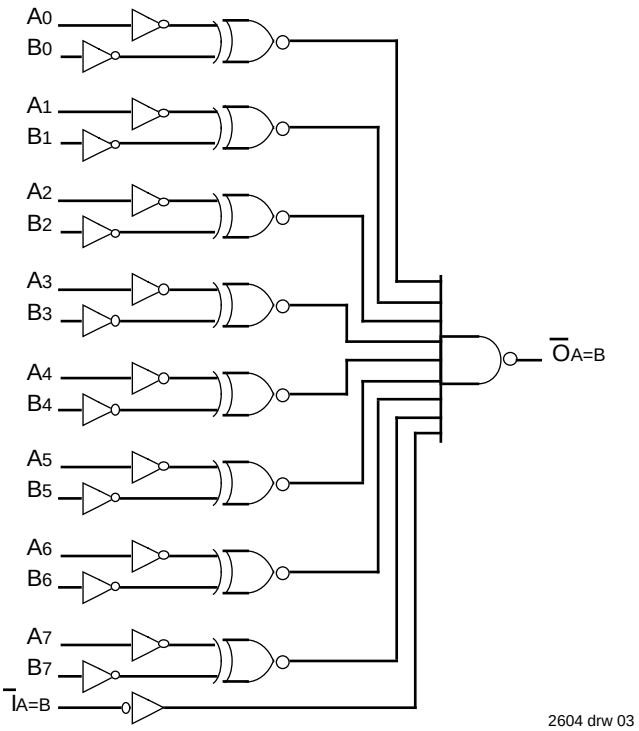
FEATURES:

- IDT54/74FCT521 equivalent to FAST™ speed
- **IDT54/74FCT521A 35% faster than FAST**
- **IDT54/74FCT521B 50% faster than FAST**
- **IDT54/74FCT521C 60% faster than FAST**
- Equivalent to FAST output drive over full temperature and voltage supply extremes
- I_{OL} = 48mA (commercial), and 32mA (military)
- CMOS power levels (1mW typ. static)
- TTL input and output level compatible
- CMOS output level compatible
- Substantially lower input current levels than FAST (5µA max.)
- Product available in Radiation Tolerant and Radiation Enhanced versions
- JEDEC standard pinout for DIP and LCC
- Military product compliant to MIL-STD-883, Class B

DESCRIPTION:

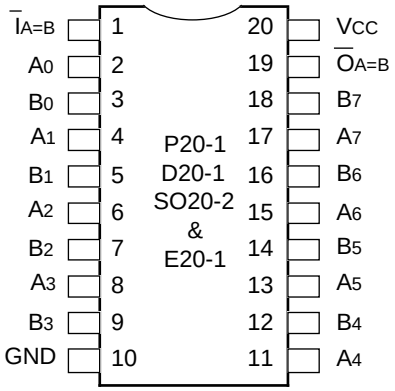
The IDT54/74FCT521/A/B/C are 8-bit identity comparators built using an advanced dual metal CMOS technology. These devices compare two words of up to eight bits each and provide a LOW output when the two words match bit for bit. The expansion input $\overline{I}_{A=B}$ also serves as an active LOW enable input.

FUNCTIONAL BLOCK DIAGRAM



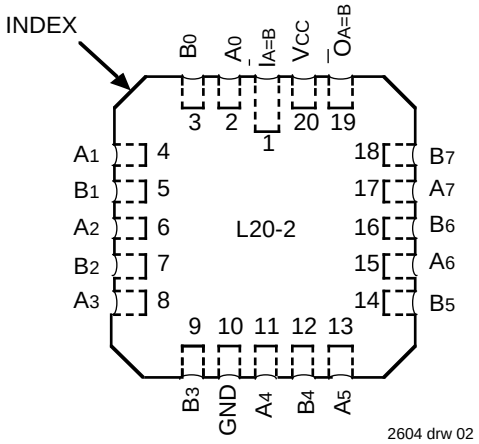
2604 drw 03

PIN CONFIGURATIONS



DIP/SOIC/CERPACK TOP VIEW

2604 drw 01



2604 drw 02

LCC TOP VIEW

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PIN DESCRIPTION

Pin Names	Description
A_0 - A_7	Word A Inputs
B_0 - B_7	Word B Inputs
$\overline{I}_{A = B}$	Expansion or Enable Input (Active LOW)
$\overline{O}_{A = B}$	Identity Output (Active LOW)

2604 tbl* 05

FUNCTION TABLE(1)

INPUTS		OUTPUT
$\overline{I}_{A = B}$	A, B	$\overline{O}_{A = B}$
L	A = B*	L
L	A ≠ B	H
H	A = B*	H
H	A ≠ B	H

NOTE:
2604 tbl* 06

1. H = HIGH Voltage Level
   L = LOW Voltage Level
   *$A_0 = B_0$, $A_1 = B_1$, $A_2 = B_2$, etc.

ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Rating	Commercial	Military	Unit
V_{TERM}(2)	Terminal Voltage with Respect to GND	–0.5 to +7.0	–0.5 to +7.0	V
V_{TERM}(3)	Terminal Voltage with Respect to GND	–0.5 to V_{CC}	–0.5 to V_{CC}	V
T_A	Operating Temperature	0 to +70	–55 to +125	°C
T_{BIAS}	Temperature Under Bias	–55 to +125	–65 to +135	°C
T_{STG}	Storage Temperature	–55 to +125	–65 to +150	°C
P_T	Power Dissipation	0.5	0.5	W
I_{OUT}	DC Output Current	120	120	mA

NOTES:
2604 tbl* 01

1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability. No terminal voltage may exceed VCC by +0.5V unless otherwise noted.
2. Input and VCC terminals only.
3. Outputs and I/O terminals only.

CAPACITANCE (T_A = +25°C, f = 1.0MHz)

Symbol	Parameter(1)	Conditions	Typ.	Max.	Unit
C_{IN}	Input Capacitance	V_{IN} = 0V	6	10	pF
C_{OUT}	Output Capacitance	V_{OUT} = 0V	8	12	pF

NOTE:
2604 tbl* 02

1. This parameter is measured at characterization but not tested.

DC ELECTRICAL CHARACTERISTICS OVER OPERATING RANGE

Following Conditions Apply Unless Otherwise Specified: V_{LC} = 0.2V; V_{HC} = V_{CC} – 0.2V
Commercial: T_A = 0°C to +70°C, V_{CC} = 5.0V ± 5%; Military: T_A = –55°C to +125°C, V_{CC} = 5.0V ± 10%

Symbol	Parameter	Test Conditions[1]		Min.	Typ.[2]	Max.	Unit
V_{IH}	Input HIGH Level	Guaranteed Logic HIGH Level		2.0	—	—	V
V_{IL}	Input LOW Level	Guaranteed Logic LOW Level		—	—	0.8	V
I_{IH}	Input HIGH Current	V_{CC} = Max.	V_I = V_{CC}	—	—	5	µA
			V_I = 2.7V	—	—	5[4]	
I_{IL}	Input LOW Current		V_I = 0.5V	—	—	–5[4]	
			V_I = GND	—	—	–5	
V_{IK}	Clamp Diode Voltage	V_{CC} = Min., I_N = –18mA		—	–0.7	–1.2	V
I_{OS}	Short Circuit Current	V_{CC} = Max.[3], V_O = GND		–60	–120	—	mA
V_{OH}	Output HIGH Voltage	V_{CC} = 3V, V_{IN} = V_{LC} or V_{HC}, I_{OH} = –32µA		V_{HC}	V_{CC}	—	V
		V_{CC} = Min.	I_{OH} = –300µA	V_{HC}	V_{CC}	—	
		V_{IN} = V_{IH} or V_{IL}	I_{OH} = –12mA MIL.	2.4	4.3	—	
			I_{OH} = –15mA COM'L.	2.4	4.3	—	
V_{OL}	Output LOW Voltage	V_{CC} = 3V, V_{IN} = V_{LC} or V_{HC}, I_{OL} = 300µA		—	GND	V_{LC}	V
		V_{CC} = Min.	I_{OL} = 300µA	—	GND	V_{LC}[4]	
		V_{IN} = V_{IH} or V_{IL}	I_{OL} = 32mA MIL.	—	0.3	0.5	
			I_{OL} = 48mA COM'L.	—	0.3	0.5	

NOTES:

2604 tbl* 03

1. For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at VCC = 5.0V, +25°C ambient and maximum loading.
3. Not more than one output should be shorted at one time. Duration of the short circuit test should not exceed one second.
4. This parameter is guaranteed but not tested.

POWER SUPPLY CHARACTERISTICS V_{LC} = 0.2V; V_{HC} = V_{CC} – 0.2V

Symbol	Parameter	Test Conditions[1]		Min.	Typ.[2]	Max.	Unit
I_{CC}	Quiescent Power Supply Current	V_{CC} = Max. $V_{IN} \geq V_{HC}$; $V_{IN} \leq V_{LC}$		—	0.2	1.5	mA
ΔI_{CC}	Quiescent Power Supply Current TTL Inputs HIGH	V_{CC} = Max. V_{IN} = 3.4V[3]		—	0.5	2.0	mA
I_{CCD}	Dynamic Power Supply Current[4]	V_{CC} = Max. Outputs Open One Input Toggling 50% Duty Cycle	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$	—	0.15	0.25	mA/ MHz
I_C	Total Power Supply Current[5]	V_{CC} = Max. Outputs Open	$V_{IN} \geq V_{HC}$ $V_{IN} \leq V_{LC}$ (FCT)	—	1.7	4.0	mA
		fi = 10MHz One Bit Toggling 50% Duty Cycle	V_{IN} = 3.4V V_{IN} = GND	—	2.0	5.0	

NOTES:

2604 tbl* 04

1. For conditions shown as Max. or Min., use appropriate value specified under Electrical Characteristics for the applicable device type.
2. Typical values are at V_{CC} = 5.0V, +25°C ambient.
3. Per TTL driven input (V_{IN} = 3.4V); all other inputs at V_{CC} or GND.
4. This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
5. $I_C = I_{QUIESCENT} + I_{INPUTS} + I_{DYNAMIC}$
   $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_{CP}/2 + f_i N_i)$
   I_{CC} = Quiescent Current
   ΔI_{CC} = Power Supply Current for a TTL High Input (V_{IN} = 3.4V)
   D_H = Duty Cycle for TTL Inputs High
   N_T = Number of TTL Inputs at D_H
   I_{CCD} = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)
   f_{CP} = Clock Frequency for Register Devices (Zero for Non-Register Devices)
   f_i = Input Frequency
   N_i = Number of Inputs at f_i
   All currents are in milliamps and all frequencies are in megahertz.

SWITCHING CHARACTERISTICS OVER OPERATING RANGE

			IDT54/74FCT521				IDT54/74FCT521A				IDT54/74FCT521B				IDT54/74FCT521C				
			Com'l.		Mil.		Com'l.		Mil.		Com'l.		Mil.		Com'l.		Mil.		
Symbol	Parameter	Condition[1]	Min.[2]	Max.	Min.[2]	Max.	Min.[2]	Max.	Min.[2]	Max.	Min.[2]	Max.	Min.[2]	Max.	Min.[2]	Max.	Min.[2]	Max.	Unit
t_{PLH} t_{PHL}	Propagation Delay An or Bn to $\overline{O}_A$ = B	C_L = 50pF R_L = 500Ω	1.5	11.0	1.5	15.0	1.5	7.2	1.5	9.5	1.5	5.5	1.5	7.3	1.5	4.5	1.5	5.1	ns
t_{PLH} t_{PHL}	Propagation Delay I_A = B to $\overline{O}_A$ = B		1.5	10.0	1.5	9.0	1.5	6.0	1.5	7.8	1.5	4.6	1.5	6.0	1.5	4.1	1.5	4.5	ns

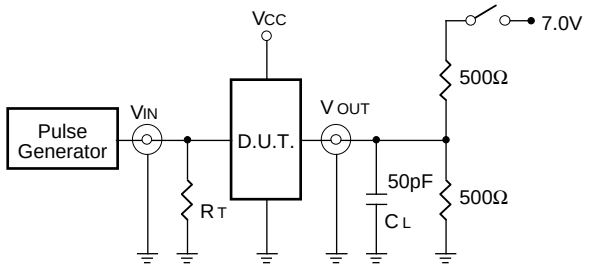
NOTES:

2604 tbl* 07

1. See test circuit and waveforms.
2. Minimum limits are guaranteed but not tested on Propagation Delays.

TEST CIRCUITS AND WAVEFORMS

TEST CIRCUITS FOR ALL OUTPUTS



SWITCH POSITION

Test	Switch
Open Drain Disable Low Enable Low	Closed
All Other Tests	Open

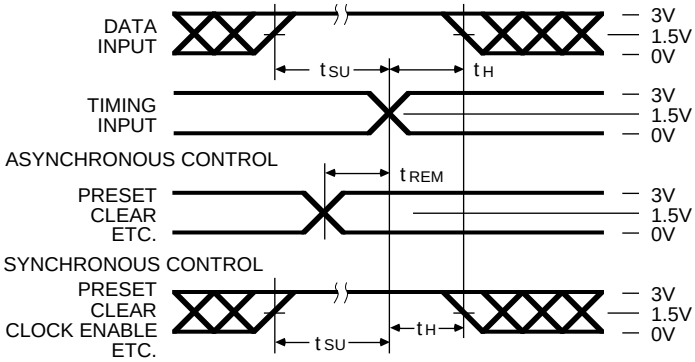
2604 tbl 08

DEFINITIONS:

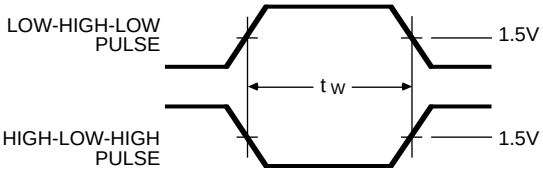
C_L = Load capacitance: includes jig and probe capacitance.

R_T = Termination resistance: should be equal to Z_{OUT} of the Pulse Generator.

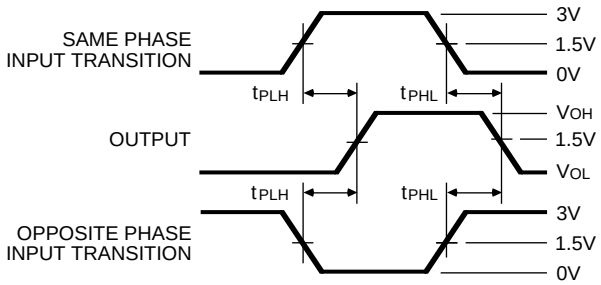
SET-UP, HOLD AND RELEASE TIMES



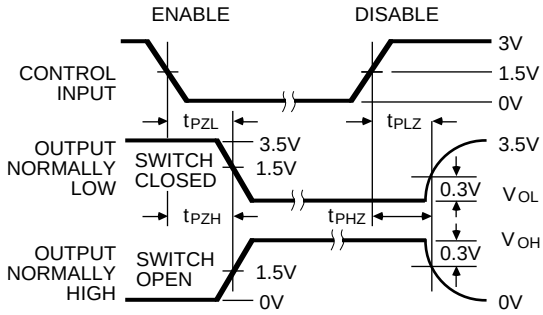
PULSE WIDTH



PROPAGATION DELAY



ENABLE AND DISABLE TIMES

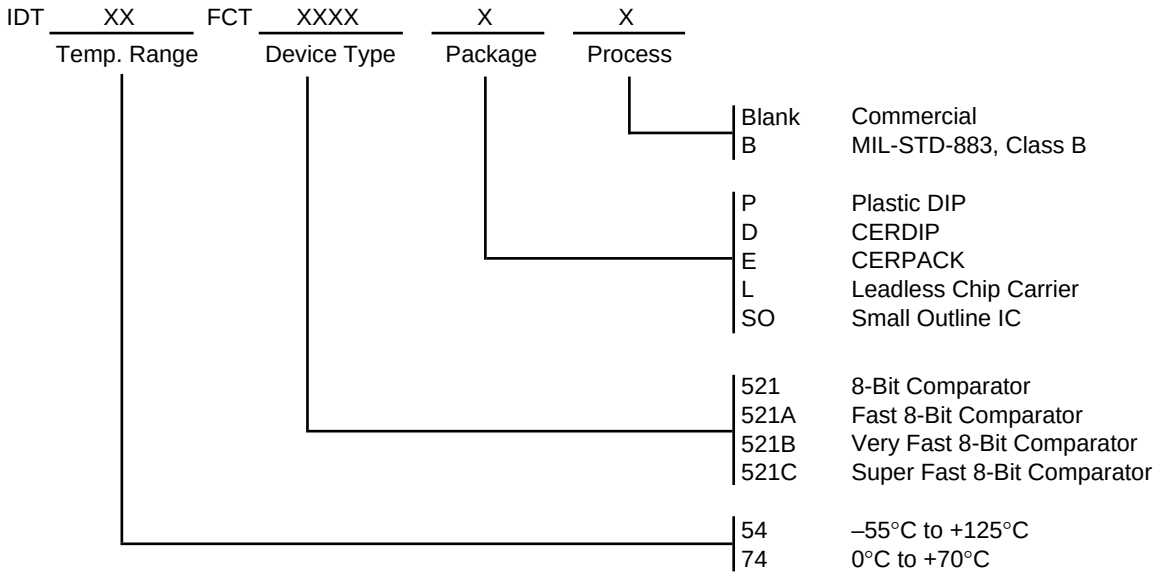


NOTES

2604 drw 04

1. Diagram shown for input Control Enable-LOW and input Control Disable-HIGH.
2. Pulse Generator for All Pulses: Rate ≤ 1.0 MHz; Z_O ≤ 50Ω; t_F ≤ 2.5ns; t_R ≤ 2.5ns.

ORDERING INFORMATION



2604 cnv* 09